STMicroelectronics - STM32L476RCT6TR Datasheet

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I²C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	51
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l476rct6tr

Table 15. STM32L476xxSTM32L476xx pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP72	WLCSP81	LQFP100	UFBGA132	LQFP144					Alternate functions	Additional functions
-	-	-	20	-	31	VREF-	S	-	-	-	-
12	G9	G9	-	J1	-	VSSA/VREF-	-	-	-	-	-
-	G8	G8	21	L1	32	VREF+	S	-	-	-	VREFBUF_ OUT
-	H9	H9	22	M1	33	VDDA	S	-	-	-	-
13	-	-	-	-	-	VDDA/VREF+	S	-	-	-	-
14	H8	H8	23	L2	34	PA0	I/O	FT_a	-	TIM2_CH1, TIM5_CH1, TIM8_ETR, USART2_CTS, UART4_TX, SAI1_EXTCLK, TIM2_ETR, EVENTOUT	OPAMP1_ VINP, ADC12_IN5, RTC_TAMP 2/WKUP1
-	-	-	-	M3	-	OPAMP1_VINM	I	TT	-	-	-
15	G4	G4	24	M2	35	PA1	I/O	FT_la	-	TIM2_CH2, TIM5_CH2, USART2_RTS_DE, UART4_RX, LCD_SEG0, TIM15_CH1N, EVENTOUT	OPAMP1_ VINM, ADC12_IN6
16	G6	G6	25	K3	36	PA2	I/O	FT_la	-	TIM2_CH3, TIM5_CH3, USART2_TX, LCD_SEG1, SAI2_EXTCLK, TIM15_CH1, EVENTOUT	ADC12_IN7, WKUP4/ LSCO
17	H7	H7	26	L3	37	PA3	I/O	TT	-	TIM2_CH4, TIM5_CH4, USART2_RX, LCD_SEG2, TIM15_CH2, EVENTOUT	OPAMP1_ VOUT, ADC12_IN8
18	J9	J9	27	E3	38	VSS	S	-	-	-	-
19	J8	J8	28	H3	39	VDD	S	-	-	-	-
20	G5	G5	29	J4	40	PA4	I/O	TT_a	-	SPI1_NSS, SPI3_NSS, USART2_CK, SAI1_FS_B, LPTIM2_OUT, EVENTOUT	ADC12_ IN9, DAC1_ OUT1
21	H6	H6	30	K4	41	PA5	I/O	TT_a	-	TIM2_CH1, TIM2_ETR, TIM8_CH1N, SPI1_SCK, LPTIM2_ETR, EVENTOUT	ADC12_ IN10, DAC1_ OUT2
22	H5	H5	31	L4	42	PA6	I/O	FT_la	-	TIM1_BKIN, TIM3_CH1, TIM8_BKIN, SPI1_MISO, USART3_CTS, QUADSPI_BK1_IO3, LCD_SEG3, TIM1_BKIN_COMP2, TIM8_BKIN_COMP2, TIM16_CH1, EVENTOUT	OPAMP2_ VINP, ADC12_ IN11

Table 15. STM32L476xxSTM32L476xx pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP72	WLCSP81	LQFP100	UFBGA132	LQFP144					Alternate functions	Additional functions
45	C1	C1	71	A12	104	PA12	I/O	FT_u	-	TIM1_ETR, USART1_RTS_DE, CAN1_TX, OTG_FS_DP, EVENTOUT	-
46	C2	C2	72	A11	105	PA13 (JTMS-SWDIO)	I/O	FT	(3)	JTMS-SWDIO, IR_OUT, OTG_FS_NOE, EVENTOUT	-
47	B1	B1	-	-	-	VSS	S	-	-	-	-
48	A1	A1	73	C11	106	VDDUSB	S	-	-	-	-
-	-	-	74	F11	107	VSS	S	-	-	-	-
-	-	-	75	G11	108	VDD	S	-	-	-	-
49	B2	B2	76	A10	109	PA14 (JTCK-SWCLK)	I/O	FT	(3)	JTCK-SWCLK, EVENTOUT	-
50	A2	A2	77	A9	110	PA15 (JTDI)	I/O	FT_l	(3)	JTDI, TIM2_CH1, TIM2_ETR, SPI1_NSS, SPI3_NSS, UART4_RTS_DE, TSC_G3_IO1, LCD_SEG17, SAI2_FS_B, EVENTOUT	-
51	D3	D3	78	B11	111	PC10	I/O	FT_l	-	SPI3_SCK, USART3_TX, UART4_TX, TSC_G3_IO2, LCD_COM4/LCD_SEG28/ LCD_SEG40, SDMMC1_D2, SAI2_SCK_B, EVENTOUT	-
52	C3	C3	79	C10	112	PC11	I/O	FT_l	-	SPI3_MISO, USART3_RX, UART4_RX, TSC_G3_IO3, LCD_COM5/LCD_SEG29/ LCD_SEG41, SDMMC1_D3, SAI2_MCLK_B, EVENTOUT	-
53	B3	B3	80	B10	113	PC12	I/O	FT_l	-	SPI3_MOSI, USART3_CK, UART5_TX, TSC_G3_IO4, LCD_COM6/LCD_SEG30/ LCD_SEG42, SDMMC1_CK, SAI2_SD_B, EVENTOUT	-
-	-	-	81	C9	114	PD0	I/O	FT	-	SPI2_NSS, DFSDM_DATIN7, CAN1_RX, FMC_D2, EVENTOUT	-

Table 17. Alternate function AF8 to AF15 (for AF0 to AF7 see Table 16) (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		UART4, UART5, LPUART1	CAN1, TSC	OTG_FS, QUADSPI	LCD	SDMMC1, COMP1, COMP2, FMC, SWPMI1	SAI1, SAI2	TIM2, TIM15, TIM16, TIM17, LPTIM2	EVENTOUT
Port E	PE0	-	-	-	LCD_SEG36	FMC_NBL0	-	TIM16_CH1	EVENTOUT
	PE1	-	-	-	LCD_SEG37	FMC_NBL1	-	TIM17_CH1	EVENTOUT
	PE2	-	TSC_G7_IO1	-	LCD_SEG38	FMC_A23	SAI1_MCLK_A	-	EVENTOUT
	PE3	-	TSC_G7_IO2	-	LCD_SEG39	FMC_A19	SAI1_SD_B	-	EVENTOUT
	PE4	-	TSC_G7_IO3	-	-	FMC_A20	SAI1_FS_A	-	EVENTOUT
	PE5	-	TSC_G7_IO4	-	-	FMC_A21	SAI1_SCK_A	-	EVENTOUT
	PE6	-	-	-	-	FMC_A22	SAI1_SD_A	-	EVENTOUT
	PE7	-	-	-	-	FMC_D4	SAI1_SD_B	-	EVENTOUT
	PE8	-	-	-	-	FMC_D5	SAI1_SCK_B	-	EVENTOUT
	PE9	-	-	-	-	FMC_D6	SAI1_FS_B	-	EVENTOUT
	PE10	-	TSC_G5_IO1	QUADSPI_CLK	-	FMC_D7	SAI1_MCLK_B	-	EVENTOUT
	PE11	-	TSC_G5_IO2	QUADSPI_NCS	-	FMC_D8	-	-	EVENTOUT
	PE12	-	TSC_G5_IO3	QUADSPI_BK1_IO0	-	FMC_D9	-	-	EVENTOUT
	PE13	-	TSC_G5_IO4	QUADSPI_BK1_IO1	-	FMC_D10	-	-	EVENTOUT
	PE14	-	-	QUADSPI_BK1_IO2	-	FMC_D11	-	-	EVENTOUT
	PE15	-	-	QUADSPI_BK1_IO3	-	FMC_D12	-	-	EVENTOUT

2. V_{IN} maximum must always be respected. Refer to *Table 20: Current characteristics* for the maximum allowed injected current values.
3. This formula has to be applied only on the power supplies related to the IO structure described in the pin definition table.
4. To sustain a voltage higher than 4 V the internal pull-up/pull-down resistors must be disabled.
5. Include VREF- pin.

Table 20. Current characteristics

Symbol	Ratings	Max	Unit
$\sum IV_{DD}$	Total current into sum of all V_{DD} power lines (source)(1)	150	mA
$\sum IV_{SS}$	Total current out of sum of all V_{SS} ground lines (sink)(1)	150	
$IV_{DD(PIN)}$	Maximum current into each V_{DD} power pin (source)(1)	100	
$IV_{SS(PIN)}$	Maximum current out of each V_{SS} ground pin (sink)(1)	100	
$I_{IO(PIN)}$	Output current sunk by any I/O and control pin except FT_f	20	
	Output current sunk by any FT_f pin	20	
	Output current sourced by any I/O and control pin	20	
$\sum I_{IO(PIN)}$	Total output current sunk by sum of all I/Os and control pins(2)	100	
	Total output current sourced by sum of all I/Os and control pins(2)	100	
$I_{INJ(PIN)}$(3)	Injected current on FT_xxx, TT_xx, RST and B pins, except PA4, PA5	-5/+0(4)	
	Injected current on PA4, PA5	-5/0	
$\sum I_{INJ(PIN)}$	Total injected current (sum of all I/Os and control pins)(5)	±25	

1. All main power (V_{DD}, V_{DDA}, V_{DDIO2}, V_{DDUSB}, V_{BAT}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supplies, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count QFP packages.
3. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
4. A positive injection is induced by $V_{IN} > V_{DDIOx}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer also to *Table 19: Voltage characteristics* for the maximum allowed input voltage values.
5. When several inputs are submitted to a current injection, the maximum $\sum I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 21. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

Table 28. Current consumption in Run and Low-power run modes, code with data processing running from SRAM1

Symbol	Parameter	Conditions			TYP					MAX[1]					Unit
		-	Voltage scaling	f_{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD}(Run)	Supply current in Run mode	$f_{HCLK} = f_{HSE}$ up to 48MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	Range 2	26 MHz	2.88	2.94	3.05	3.23	3.58	3.18	3.26	3.40	4.02	4.65	mA
				16 MHz	1.83	1.87	1.98	2.15	2.50	2.01	2.16	2.30	2.72	3.34	
				8 MHz	0.97	1.00	1.11	1.27	1.62	1.07	1.16	1.32	1.73	2.36	
				4 MHz	0.54	0.57	0.67	0.84	1.18	0.59	0.69	0.88	1.23	1.96	
				2 MHz	0.33	0.36	0.46	0.62	0.96	0.37	0.45	0.63	0.98	1.70	
				1 MHz	0.22	0.25	0.35	0.51	0.85	0.25	0.33	0.50	0.86	1.57	
				100 kHz	0.12	0.15	0.25	0.41	0.75	0.15	0.21	0.39	0.74	1.45	
			Range 1	80 MHz	10.2	10.3	10.5	10.7	11.1	11.22	11.57	11.86	12.07	13.11	
				72 MHz	9.25	9.31	9.46	9.68	10.1	10.18	10.41	10.55	10.76	11.80	
				64 MHz	8.25	8.31	8.46	8.67	9.08	9.08	9.37	9.66	9.87	10.91	
				48 MHz	6.26	6.33	6.48	6.69	7.11	6.89	7.11	7.25	7.67	8.50	
				32 MHz	4.22	4.28	4.42	4.63	5.03	4.64	4.86	5.15	5.56	6.19	
				24 MHz	3.20	3.25	3.38	3.59	3.99	3.52	3.70	3.84	4.26	5.09	
				16 MHz	2.18	2.22	2.35	2.55	2.94	2.40	2.55	2.84	3.25	4.09	
I_{DD}(LPRun)	Supply current in low-power run mode	$f_{HCLK} = f_{MSI}$ all peripherals disable FLASH in power-down		2 MHz	242	275	384	562	924	300	380	573	927	1677	µA
				1 MHz	130	162	269	445	809	180	243	435	810	1560	
				400 kHz	61	90	197	374	734	95	160	353	728	1478	
				100 kHz	26	56	163	339	702	55	122	314	679	1429	

1. Guaranteed by characterization results, unless otherwise specified.

Table 30. Typical current consumption in Run and Low-power run modes, with different codes running from Flash, ART disable

Symbol	Parameter	Conditions -	Voltage scaling	Code	TYP 25 °C	Unit	TYP 25 °C	Unit
I_{DD}(Run)	Supply current in Run mode	$f_{HCLK} = f_{HSE}$ up to 48 MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	Range 2 f_{HCLK} = 26 MHz	Reduced code(1)	3.1	mA	119	µA/MHz
				Coremark	2.9		111	
				Dhrystone 2.1	2.8		111	
				Fibonacci	2.7		104	
				While(1)	2.6		100	
			Range 1 f_{HCLK} = 80 MHz	Reduced code(1)	10.0	mA	125	µA/MHz
				Coremark	9.4		117	
				Dhrystone 2.1	9.1		114	
				Fibonacci	9.0		112	
				While(1)	9.3		116	
I_{DD}(LPRun)	Supply current in Low-power run	$f_{HCLK} = f_{MSI}$ = 2 MHz all peripherals disable		Reduced code(1)	358	µA	179	µA/MHz
				Coremark	392		196	
				Dhrystone 2.1	390		195	
				Fibonacci	385		192	
				While(1)	385		192	

1. Reduced code used for characterization results provided in *Table 26*, *Table 27*, *Table 28*.

Table 31. Typical current consumption in Run and Low-power run modes, with different codes running from SRAM1

Symbol	Parameter	Conditions -	Voltage scaling	Code	TYP 25 °C	Unit	TYP 25 °C	Unit
I_{DD}(Run)	Supply current in Run mode	$f_{HCLK} = f_{HSE}$ up to 48 MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	Range 2 f_{HCLK} = 26 MHz	Reduced code(1)	2.9	mA	111	µA/MHz
				Coremark	2.9		111	
				Dhrystone 2.1	2.9		111	
				Fibonacci	2.6		100	
				While(1)	2.6		100	
			Range 1 f_{HCLK} = 80 MHz	Reduced code(1)	10.2	mA	127	µA/MHz
				Coremark	10.4		130	
				Dhrystone 2.1	10.3		129	
				Fibonacci	9.6		120	
				While(1)	9.3		116	
I_{DD}(LPRun)	Supply current in Low-power run	$f_{HCLK} = f_{MSI}$ = 2 MHz all peripherals disable		Reduced code(1)	242	µA	121	µA/MHz
				Coremark	242		121	
				Dhrystone 2.1	242		121	
				Fibonacci	225		112	
				While(1)	242		121	

1. Reduced code used for characterization results provided in *Table 26*, *Table 27*, *Table 28*.

Low-speed external user clock generated from an external source

In bypass mode the LSE oscillator is switched off and the input pin is a standard GPIO.

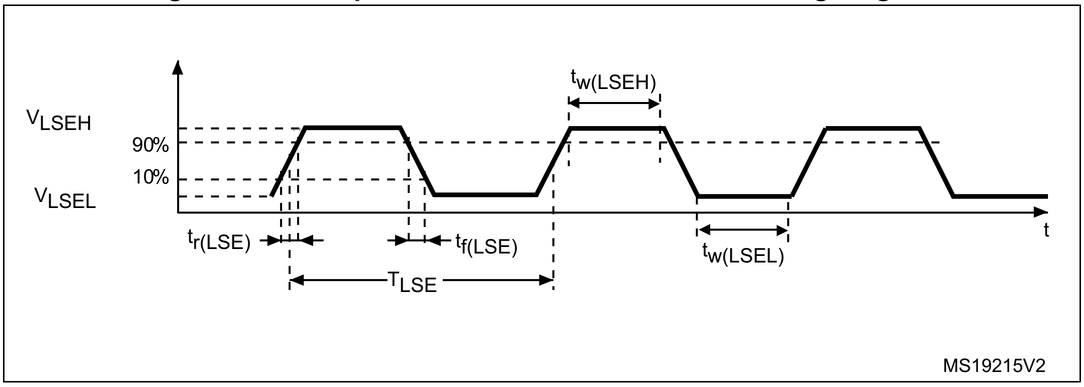
The external clock signal has to respect the I/O characteristics in Section 6.3.14. However, the recommended clock input waveform is shown in Figure 17.

Table 44. Low-speed external user clock characteristics[1]

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User external clock source frequency	-	-	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage	-	0.7 V_{DDIOx}	-	V_{DDIOx}	V
V_{LSEL}	OSC32_IN input pin low level voltage	-	V_{SS}	-	0.3 V_{DDIOx}	V
$t_{w(LSEH)}$ $t_{w(LSEL)}$	OSC32_IN high or low time	-	250	-	-	ns

1. Guaranteed by design.

Figure 17. Low-speed external clock source AC timing diagram



6.3.8 Internal clock source characteristics

The parameters given in Table 47 are derived from tests performed under ambient temperature and supply voltage conditions summarized in Table 22: General operating conditions. The provided curves are characterization results, not tested in production.

High-speed internal (HSI16) RC oscillator

Table 47. HSI16 oscillator characteristics[1]

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI16}	HSI16 Frequency	V_{DD}=3.0 V, T_A=30 °C	15.88	-	16.08	MHz
TRIM	HSI16 user trimming step	Trimming code is not a multiple of 64	0.2	0.3	0.4	%
		Trimming code is a multiple of 64	-4	-6	-8	
DuCy(HSI16)[2]	Duty Cycle	-	45	-	55	%
Δ_{Temp}(HSI16)	HSI16 oscillator frequency drift over temperature	T_A= 0 to 85 °C	-1	-	1	%
		T_A= -40 to 125 °C	-2	-	1.5	%
Δ_{VDD}(HSI16)	HSI16 oscillator frequency drift over V_{DD}	V_{DD}=1.62 V to 3.6 V	-0.1	-	0.05	%
t_{su}(HSI16)[2]	HSI16 oscillator start-up time	-	-	0.8	1.2	μs
t_{stab}(HSI16)[2]	HSI16 oscillator stabilization time	-	-	3	5	μs
I_{DD}(HSI16)[2]	HSI16 oscillator power consumption	-	-	155	190	μA

1. Guaranteed by characterization results.
2. Guaranteed by design.

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 54. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{HCLK}]		Unit
				f_{MSI} = 24 MHz	8 MHz/ 80 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, LQFP144 package compliant with IEC 61967-2	0.1 to 30 MHz	-9	2	dBµV
			30 to 130 MHz	-8	3	
			130 MHz to 1 GHz	-10	14	
			EMI Level	1.5	3.5	-

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

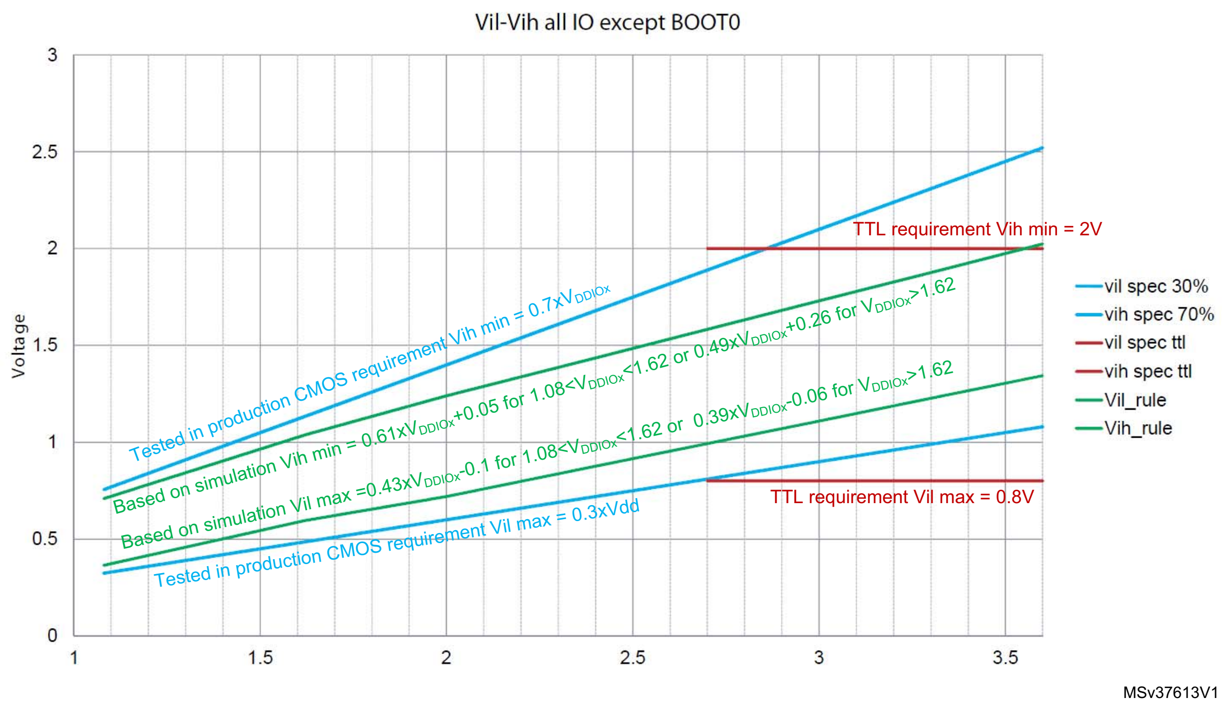
Table 55. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to ANSI/ESDA/JEDEC JS-001	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD STM5.3.1	C3	250	

1. Guaranteed by characterization results.

All I/Os are CMOS- and TTL-compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in *Figure 22* for standard I/Os, and in *Figure 22* for 5 V tolerant I/Os.

Figure 22. I/O input characteristics



Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ±8 mA, and sink or source up to ± 20 mA (with a relaxed V_{OL}/V_{OH}).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on V_{DDIOx}, plus the maximum consumption of the MCU sourced on V_{DD}, cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 19: Voltage characteristics*).
- The sum of the currents sunk by all the I/Os on V_{SS}, plus the maximum consumption of the MCU sunk on V_{SS}, cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 19: Voltage characteristics*).

Table 68. ADC accuracy - limited test conditions 4(1)(2)(3) (continued)

<table>
<tr><th>Sym-bol</th><th>Parameter</th><th colspan="3">Conditions(4)</th><th>Min</th><th>Typ</th><th>Max</th><th>Unit</th></tr>
<tr><td rowspan="4">THD</td><td rowspan="4">Total harmonic distortion</td><td rowspan="4">ADC clock frequency ≤ 26 MHz,
1.65 V ≤ V_{DDA} = VREF+ ≤ 3.6 V,
Voltage scaling Range 2</td><td rowspan="2">Single ended</td><td>Fast channel (max speed)</td><td>-</td><td>-71</td><td>-69</td><td rowspan="4">dB</td></tr>
<tr><td>Slow channel (max speed)</td><td>-</td><td>-71</td><td>-69</td></tr>
<tr><td rowspan="2">Differential</td><td>Fast channel (max speed)</td><td>-</td><td>-73</td><td>-72</td></tr>
<tr><td>Slow channel (max speed)</td><td>-</td><td>-73</td><td>-72</td></tr>
</table>

1. Guaranteed by design.
2. ADC DC accuracy values are measured after internal calibration.
3. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
4. The I/O analog switch voltage booster is enable when V_{DDA} < 2.4 V (BOOSTEN = 1 in the SYSCFG_CFGR1 when V_{DDA} < 2.4 V). It is disable when V_{DDA} ≥ 2.4 V. No oversampling.

Figure 25. ADC accuracy characteristics

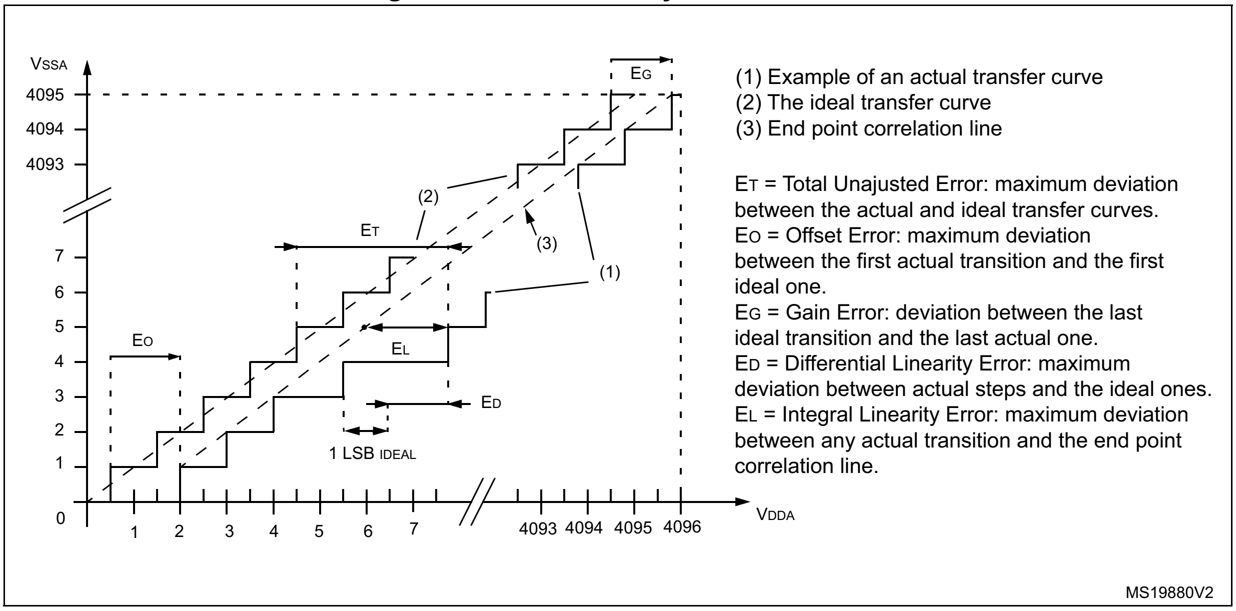
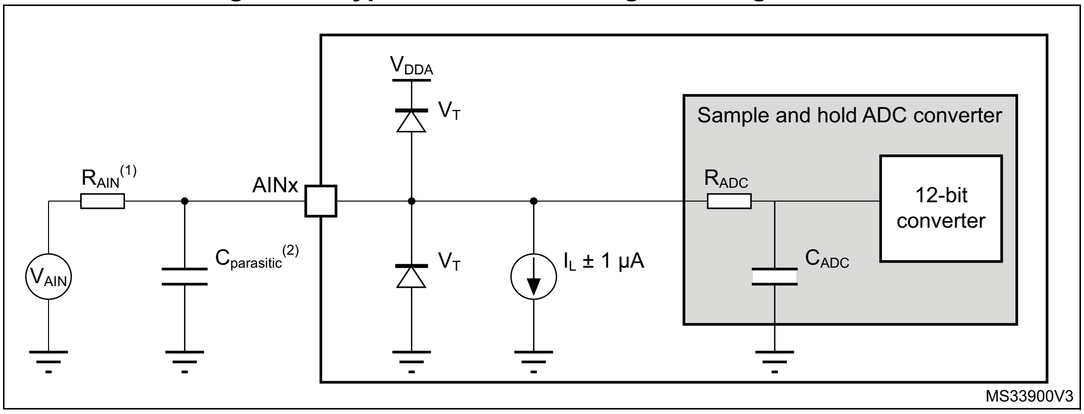


Figure 26. Typical connection diagram using the ADC



1. Refer to *Table 63: ADC characteristics* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 13: Power supply scheme*. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

6.3.24 LCD controller characteristics

The devices embed a built-in step-up converter to provide a constant LCD reference voltage independently from the V_{DD} voltage. An external capacitor C_{ext} must be connected to the VLCD pin to decouple this converter.

Table 77. LCD controller characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{LCD}	LCD external voltage		-	-	3.6	V
V_{LCD0}	LCD internal reference voltage 0		-	2.62	-	V
V_{LCD1}	LCD internal reference voltage 1		-	2.76	-	V
V_{LCD2}	LCD internal reference voltage 2		-	2.89	-	V
V_{LCD3}	LCD internal reference voltage 3		-	3.04	-	V
V_{LCD4}	LCD internal reference voltage 4		-	3.19	-	V
V_{LCD5}	LCD internal reference voltage 5		-	3.32	-	V
V_{LCD6}	LCD internal reference voltage 6		-	3.46	-	V
V_{LCD7}	LCD internal reference voltage 7		-	3.62	-	V
C_{ext}	V_{LCD} external capacitance	Buffer OFF (BUFEN=0 is LCD_CR register)	0.2	-	2	µF
		Buffer ON (BUFEN=1 is LCD_CR register)	1	-	2	
I_{LCD}(2)	Supply current from V_{DD} at V_{DD} = 2.2 V	Buffer OFF (BUFEN=0 is LCD_CR register)	-	3	-	µA
	Supply current from V_{DD} at V_{DD} = 3.0 V	Buffer OFF (BUFEN=0 is LCD_CR register)	-	1.5	-	
I_{VLCD}	Supply current from V_{LCD} (V_{LCD} = 3 V)	Buffer OFF (BUFFEN = 0, PON = 0)	-	0.5	-	µA
		Buffer ON (BUFFEN = 1, 1/2 Bias)	-	0.6	-	
		Buffer ON (BUFFEN = 1, 1/3 Bias)	-	0.8	-	
		Buffer ON (BUFFEN = 1, 1/4 Bias)	-	1	-	
R_{HN}	Total High Resistor value for Low drive resistive network		-	5.5	-	MΩ
R_{LN}	Total Low Resistor value for High drive resistive network		-	240	-	kΩ
V_{44}	Segment/Common highest level voltage		-	V_{LCD}	-	V
V_{34}	Segment/Common 3/4 level voltage		-	3/4 V_{LCD}	-	V
V_{23}	Segment/Common 2/3 level voltage		-	2/3 V_{LCD}	-	V
V_{12}	Segment/Common 1/2 level voltage		-	1/2 V_{LCD}	-	V
V_{13}	Segment/Common 1/3 level voltage		-	1/3 V_{LCD}	-	V
V_{14}	Segment/Common 1/4 level voltage		-	1/4 V_{LCD}	-	V
V_0	Segment/Common lowest level voltage		-	0	-	V

Table 86. SAI characteristics[(1)] (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{v(SD\_B\_ST)}$	Data output valid time	Slave transmitter (after enable edge) $2.7 \le V_{DD} \le 3.6$	-	22	ns
		Slave transmitter (after enable edge) $1.71 \le V_{DD} \le 3.6$	-	34	
$t_{h(SD\_B\_ST)}$	Data output hold time	Slave transmitter (after enable edge)	10	-	ns
$t_{v(SD\_A\_MT)}$	Data output valid time	Master transmitter (after enable edge) $2.7 \le V_{DD} \le 3.6$	-	27	ns
		Master transmitter (after enable edge) $1.71 \le V_{DD} \le 3.6$	-	40	
$t_{h(SD\_A\_MT)}$	Data output hold time	Master transmitter (after enable edge)	10	-	ns

1. Guaranteed by characterization results.
2. APB clock frequency must be at least twice SAI clock frequency.

Figure 33. SAI master timing waveforms

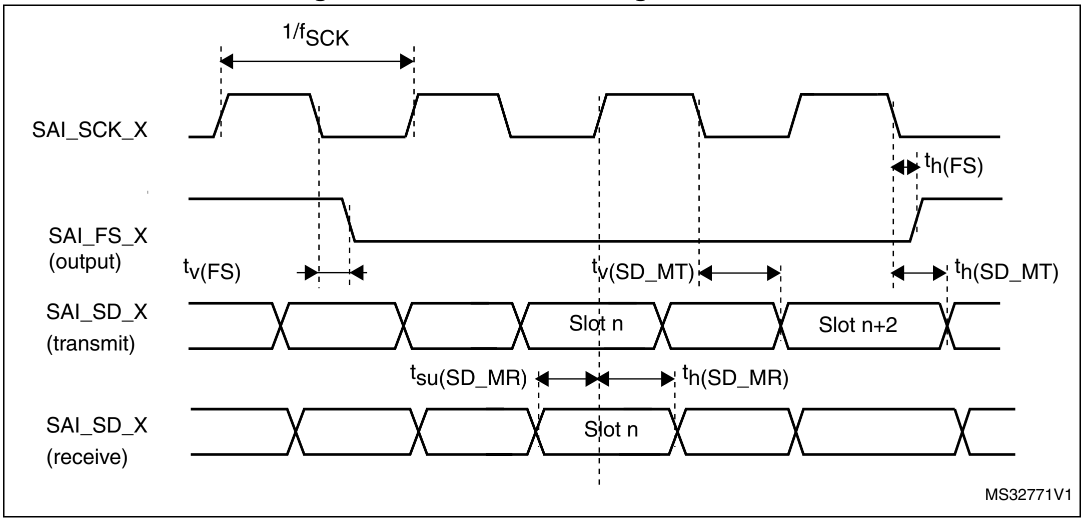


Table 87. SD / MMC dynamic characteristics, V_{DD}=2.7 V to 3.6 V[(1)] (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
CMD, D outputs (referenced to CK) in SD default mode						
t_{OVD}	Output valid default time SD	f_{PP} = 50 MHz	-	4.5	5	ns
t_{OHD}	Output hold default time SD	f_{PP} = 50 MHz	0	-	-	ns

1. Guaranteed by characterization results.

Table 88. eMMC dynamic characteristics, V_{DD} = 1.71 V to 1.9 V[(1)(2)]

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDIO_CK/f_{PCLK2} frequency ratio	-	-	-	4/3	-
$t_{W(CKL)}$	Clock low time	f_{PP} = 50 MHz	8	10	-	ns
$t_{W(CKH)}$	Clock high time	f_{PP} = 50 MHz	8	10	-	ns
CMD, D inputs (referenced to CK) in eMMC mode						
t_{ISU}	Input setup time HS	f_{PP} = 50 MHz	0	-	-	ns
t_{IH}	Input hold time HS	f_{PP} = 50 MHz	5	-	-	ns
CMD, D outputs (referenced to CK) in eMMC mode						
t_{OV}	Output valid time HS	f_{PP} = 50 MHz	-	13.5	15.5	ns
t_{OH}	Output hold time HS	f_{PP} = 50 MHz	9	-	-	ns

1. Guaranteed by characterization results.
2. C_{LOAD} = 20pF.

Figure 35. SDIO high-speed mode

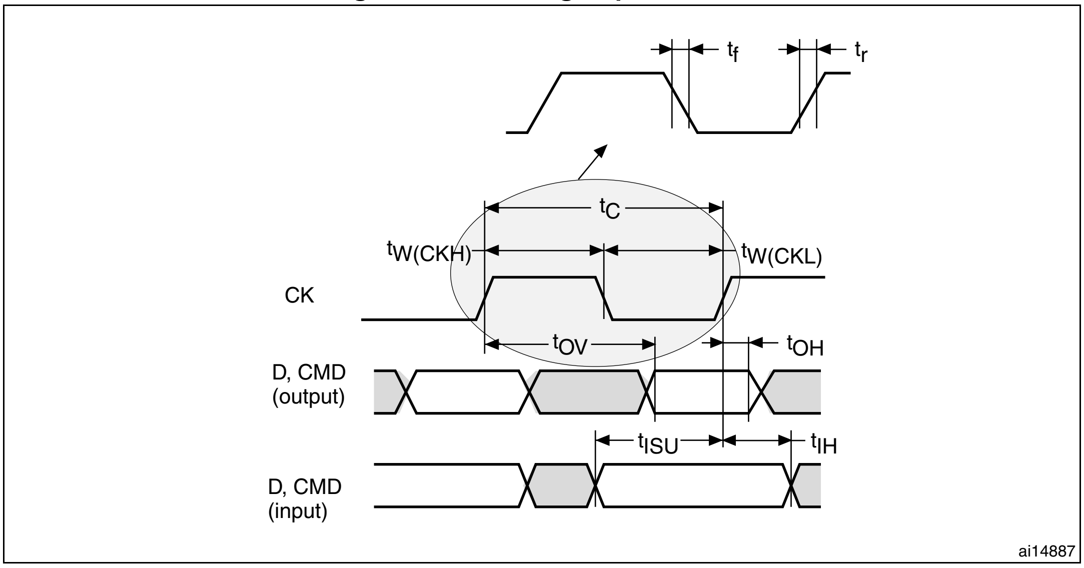


Table 105. UFBGA132 - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches[(1)]		
	Min	Typ	Max	Min	Typ	Max
e	-	0.500	-	-	0.0197	-
Z	-	0.750	-	-	0.0295	-
ddd	-	0.080	-	-	0.0031	-
eee	-	0.150	-	-	0.0059	-
fff	-	0.050	-	-	0.0020	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 53. UFBGA132 - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package recommended footprint

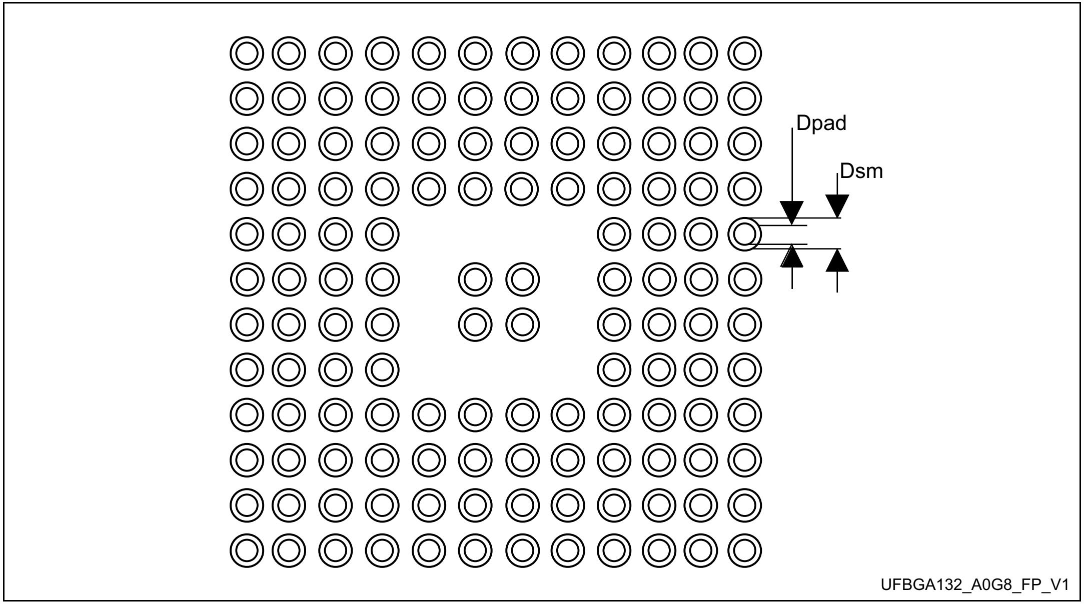
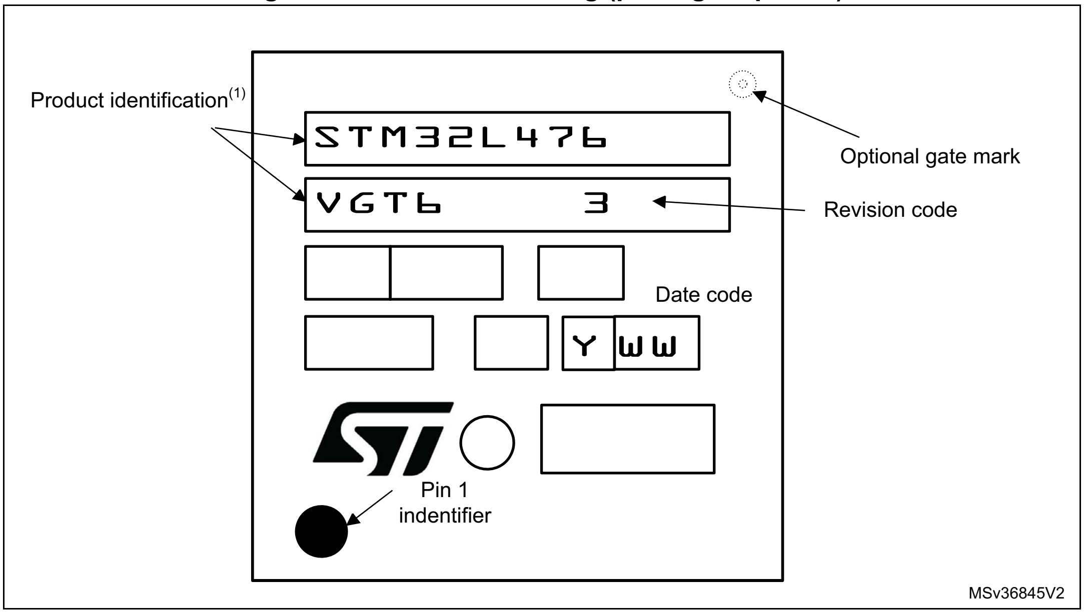


Table 106. UFBGA132 recommended PCB design rules (0.5 mm pitch BGA)

Dimension	Recommended values
Pitch	0.5 mm
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm
Ball diameter	0.280 mm

Figure 57. LQFP100 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

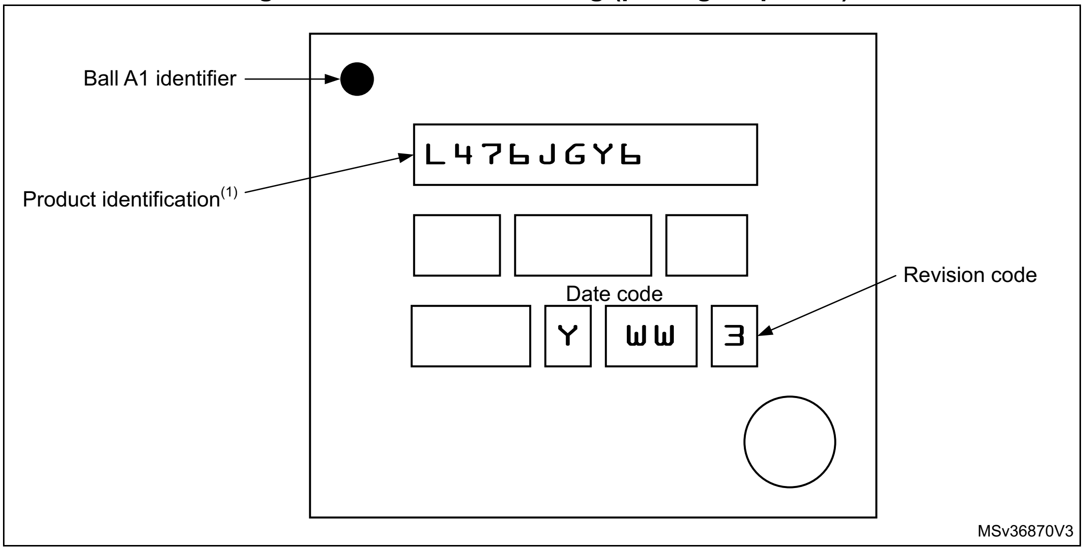
Table 111. WLCSP72 recommended PCB design rules (0.4 mm pitch BGA)

Dimension	Recommended values
Pitch	0.4 mm
Dpad	0.225 mm
Dsm	0.290 mm typ. (depends on the solder mask registration tolerance)
Stencil opening	0.250 mm
Stencil thickness	0.100 mm

Device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Figure 63. WLCSP72 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.